HS1DFSH – HS1MFSH

Taiwan Semiconductor

1A, 200V - 1000V High Efficient Surface Mount Rectifier

FEATURES

- AEC-Q101 qualified
- Glass passivated chip junction
- Ideal for automated placement
- Low power loss, high efficiency
- Fast switching for high efficiency
- Low profile package
- Moisture sensitivity level: level 1, per J-STD-020
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Freewheeling
- Snubber
- DC/DC converters
- Automotive application

MECHANICAL DATA

- Case: SOD-128
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 2 whisker test
- Polarity: Indicated by cathode band
- Weight: 0.028g (approximately)

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)								
PARAMETER		SYMBOL	HS1D	HS1G	HS1J	HS1K	HS1M	UNIT
PARAIVIE I ER		STMBUL	FSH	FSH	FSH	FSH	FSH	UNIT
Marking code on the device			HS1DFH	HS1GFH	HS1JFH	HS1KFH	HS1MFH	
Repetitive peak reverse voltage		V _{RRM}	200	400	600	800	1000	V
Reverse voltage, total rms value		V _{R(RMS)}	140	280	420	560	700	V
Forward current		I _F			1			А
Surge peak forward current, single half sine-wave	t = 8.3ms				35			А
superimposed on rated load	t = 1.0ms	I _{FSM}			90			А
Junction temperature		TJ	-55 to +150			°C		
Storage temperature		T _{STG}	-55 to +150			°C		

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KEY PARAMETERS PARAMETER VALUE UNIT I_{F} 1 А V_{RRM} 200 - 1000 V I_{FSM} 35 A °C 150 T_{J MAX} Package SOD-128 Configuration Single die







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THERMAL PERFORMANCE				
PARAMETER	SYMBOL	ТҮР	UNIT	
Junction-to-lead thermal resistance	R _{eJL}	29	°C/W	
Junction-to-ambient thermal resistance	R _{eja}	51	°C/W	
Junction-to-case thermal resistance	R _{eJC}	22	°C/W	

Thermal Performance Note: Units mounted on PCB (5mm x 5mm Cu pad test board)

PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
		$I_F = 0.5A, T_J = 25^{\circ}C$		0.80	-	V
	HS1DFSH	$I_F = 1.0A, T_J = 25^{\circ}C$		0.85	1.00	V
		$I_F = 0.5A, T_J = 125^{\circ}C$		0.65	-	V
		$I_F = 1.0A, T_J = 125^{\circ}C$		0.71	0.80	V
		$I_F = 0.5A, T_J = 25^{\circ}C$		0.84	-	V
		$I_F = 1.0A, T_J = 25^{\circ}C$		0.91	1.30	V
	HS1GFSH	$I_F = 0.5A, T_J = 125^{\circ}C$	V _F	0.68	-	V
– , , (1)		$I_F = 1.0A, T_J = 125^{\circ}C$		0.76	0.86	V
Forward voltage ⁽¹⁾		$I_F = 0.5A, T_J = 25^{\circ}C$		0.92	-	V
		$I_F = 1.0A, T_J = 25^{\circ}C$		1.02	1.70	V
	HS1JFSH	$I_F = 0.5A, T_J = 125^{\circ}C$		0.73	-	V
		$I_F = 1.0A, T_J = 125^{\circ}C$		0.83	1.02	V
	HS1KFSH HS1MFSH	$I_F = 0.5A, T_J = 25^{\circ}C$		1.32	-	V
		$I_F = 1.0A, T_J = 25^{\circ}C$		1.49	1.70	V
		$I_F = 0.5A, T_J = 125^{\circ}C$		0.98	-	V
		$I_F = 1.0A, T_J = 125^{\circ}C$		1.16	1.39	V
Reverse current @ rated V _R ⁽²⁾		$T_J = 25^{\circ}C$	- I _R	-	1	μA
		T _J = 125°C		-	35	μA
	HS1DFSH HS1GFSH		t _{rr}	-	50	ns
Reverse recovery time	HS1JFSH HS1KFSH HS1MFSH	I _F = 0.5A, I _R = 1.0A, I _{rr} = 0.25A		-	75	ns
	HS1DFSH		CJ	20	-	pF
	HS1GFSH			17	-	pF
Junction capacitance	HS1JFSH	1MHz, V _R = 4.0V		13	-	pF
	HS1KFSH HS1MFSH	1		8	-	pF

Notes:

(1) Pulse test with PW = 0.3ms

(2) Pulse test with PW = 30ms



ORDERING INFORMATION

ORDERING CODE ⁽¹⁾	PACKAGE	PACKING
HS1xFSH	SOD-128	14,000 / Tape & Reel

Notes:

(1) "x" defines voltage from 200V(HS1DFSH) to 1000V(HS1MFSH)



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Fig.1 Forward Current Derating Curve

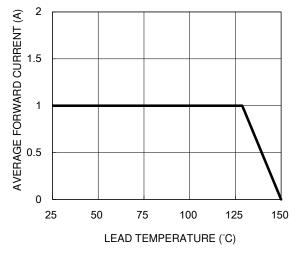
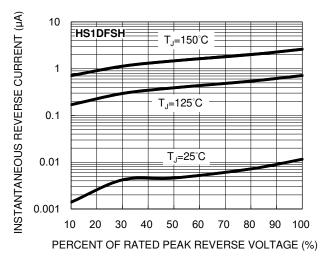
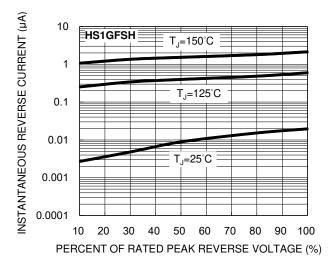


Fig.3 Typical Reverse Characteristics







1000 HS1DFSH HS1GFSH HS1JFSH HS1KSH to HS1MFSH 100 10 f=1.0MHz Vsig=50mVp-p 1 10 REVERSE VOLTAGE (V)

Fig.2 Typical Junction Capacitance

Fig.4 Typical Forward Characteristics

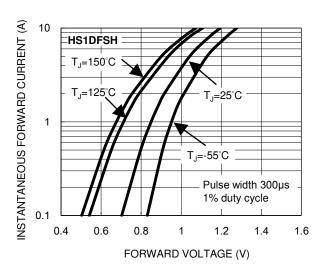
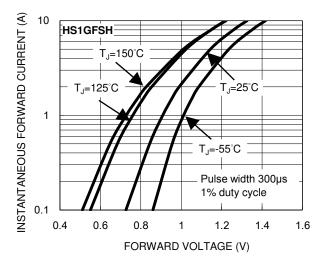


Fig.6 Typical Forward Characteristics

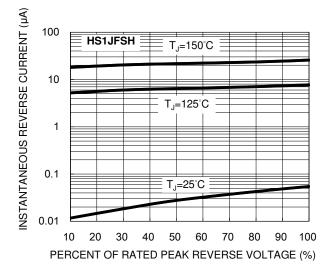




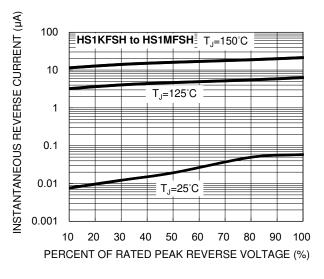
CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

Fig.7 Typical Reverse Characteristics







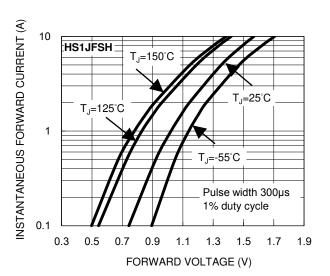
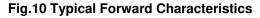
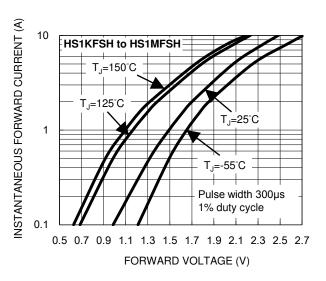


Fig.8 Typical Forward Characteristics





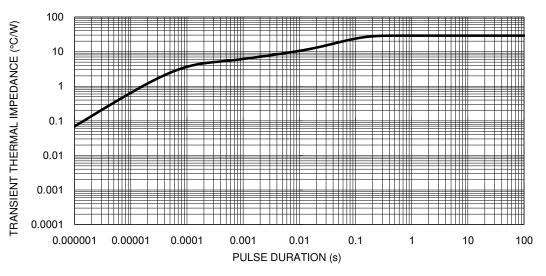


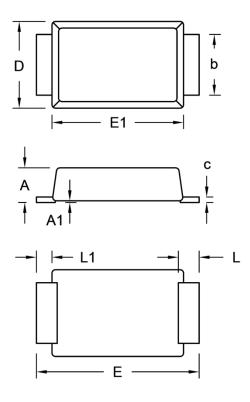
Fig.11 Typical Transient Thermal Impedance



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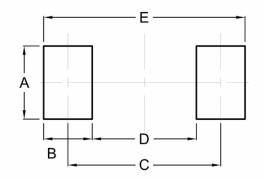
PACKAGE OUTLINE DIMENSIONS

SOD-128



DIM.	Unit	(mm)	Unit	inch)	
	Min.	Max.	Min.	Max.	
A	0.90	1.10	0.035	0.043	
A1	0.00	0.10	0.000	0.004	
b	1.60	1.90	0.063	0.075	
с	0.10	0.22	0.004	0.009	
D	2.30	2.70	0.091	0.106	
E	4.40	5.00	0.173	0.197	
E1	3.60	4.00	0.142	0.157	
L	0.40	0.80	0.016	0.031	
L1	0.30	0.60	0.012	0.024	

SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
A	2.10	0.083
В	1.40	0.055
С	4.40	0.173
D	3.00	0.118
E	5.80	0.228

MARKING DIAGRAM



P/N	= Marking Code
YW	= Date Code
F	= Factory Code



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